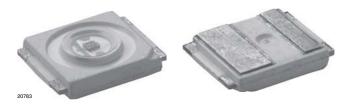
AUTOMOTIVE



### Vishay Semiconductors

# High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology



VSMY7852X01 is an infrared, 850 nm emitting diode based

on surface emitter technology with high radiant power and

high speed, molded in low thermal resistance Little Star

package. A 20 mil chip provides outstanding low forward

voltage and allows DC operation of the device up to 250 mA.

### **FFEATURES**

• Package type: surface mount

Package form: Little Star®

• Dimensions (L x W x H in mm): 6.0 x 7.0 x 1.5

Peak wavelength: λ<sub>p</sub> = 850 nm

- · High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 60^{\circ}$
- Low forward voltage
- Designed for high drive currents: up to 250 mA DC and up to 1.5 A pulses
- Low thermal resistance: R<sub>thJP</sub> = 15 K/W
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- AEC-Q101 qualified
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

### **AAPPLICATIONS**

- Infrared illumination for CMOS cameras (CCTV)
- Driver assistance systems
- Machine vision IR data transmission

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (deg)	λ <sub>p</sub> (nm)	t <sub>r</sub> (ns)	
VSMY7852X01	42	± 60	850	15	

### Note

**DESCRIPTION** 

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VSMY7852X01-GS08	Tape and reel	MOQ: 2000 pcs, 2000 pcs/reel	Little Star		

#### Note

· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		$V_{R}$	5	V	
Forward current		I <sub>F</sub>	250	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	500	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1.5	Α	
Power dissipation		$P_V$	500	mW	
Junction temperature		Tj	125	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	Acc. figure 7, J-STD-20	T <sub>sd</sub>	260	°C	
Thermal resistance junction/pin	Acc. J-STD-051, soldered on PCB	$R_{thJP}$	15	K/W	

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For technical questions, contact: <a href="mailto:emittertechsupport@vishay.com">emittertechsupport@vishay.com</a>

# Vishay Semiconductors High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology

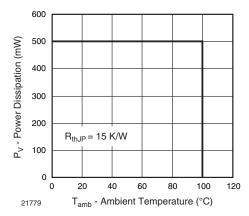


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

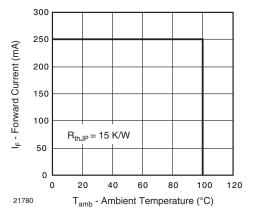


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 250 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>		1.8	2.0	V
	$I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$	V <sub>F</sub>		2.8		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>		- 1.5		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>	not designed for reverse operation			μΑ
Dedient intensity	$I_F = 250 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	30	42	90	mW/sr
Radiant intensity	$I_F = 1.5 \text{ A}, t_p = 100 \mu s$	l <sub>e</sub>		220		mW/sr
Radiant power	$I_F = 250 \text{ mA}, t_p = 20 \text{ ms}$	фe		130		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 1 A	TKφ <sub>e</sub>		- 0.5		%/K
Angle of half intensity		φ		± 60		deg
Peak wavelength	I <sub>F</sub> = 250 mA	$\lambda_{p}$		850		nm
Spectral bandwidth	I <sub>F</sub> = 250 mA	Δλ		30		nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 250 mA	ΤΚλρ		0.2		nm/K
Rise time	I <sub>F</sub> = 250 mA	t <sub>r</sub>		8		ns
Fall time	I <sub>F</sub> = 250 mA	t <sub>f</sub>		10		ns



# High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology

### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

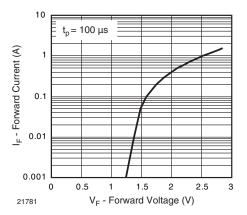


Fig. 3 - Forward Current vs. Forward Voltage

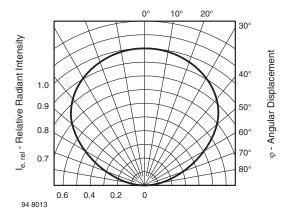


Fig. 6 - Relative Radiant Intensity vs. Angular Displacement

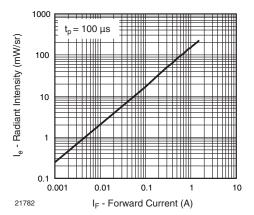


Fig. 4 - Radiant Intensity vs. Forward Current

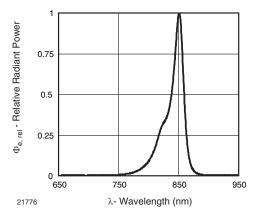
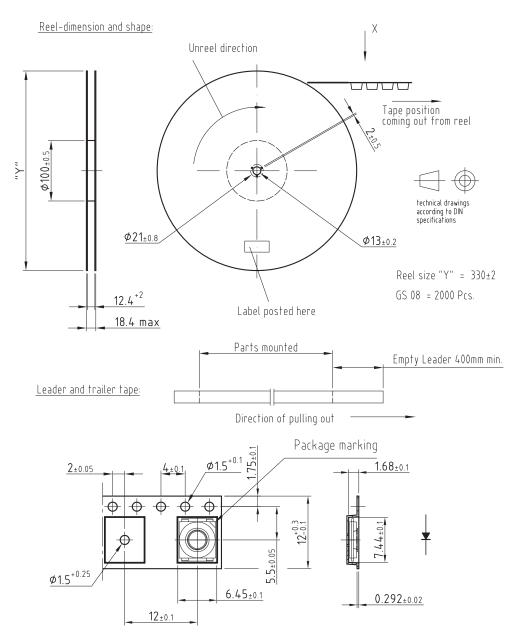


Fig. 5 - Relative Radiant Power vs. Wavelength

### Vishay Semiconductors High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology



### **TAPING DIMENSIONS** in millimeters



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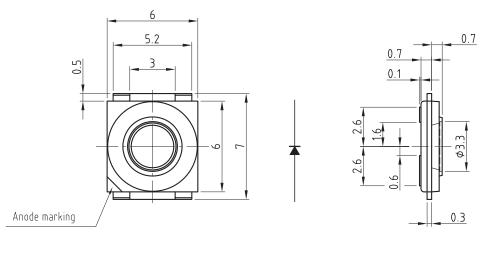
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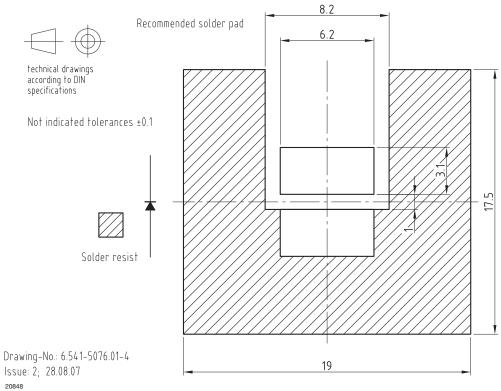
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# High Power Infrared Emitting Diode, Vishay Semiconductors 850 nm, Surface Emitter Technology

### **PACKAGE DIMENISONS** in millimeters





# Vishay Semiconductors High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology



### **SOLDER PROFILE**

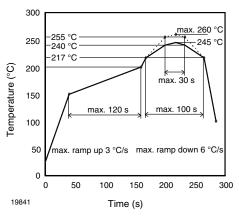


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020 for Preconditioning acc. to JEDEC, Level 2a

### **DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

#### **FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

Conditions:  $T_{amb}$  < 30 °C, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020B

#### **DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40  $^{\circ}$ C (+ 5  $^{\circ}$ C), RH < 5  $^{\circ}$ M.



## **Legal Disclaimer Notice**

Vishay

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